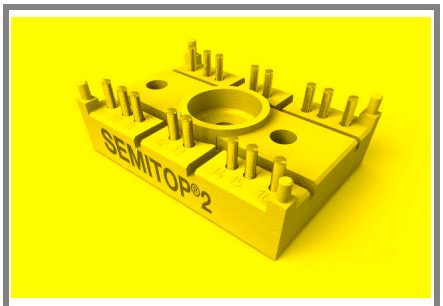
# SK50GARL065




**SEMITOP® 2**

## IGBT Module

**SK50GARL065**

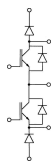
Preliminary Data

### Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N-channel homogeneous silicon structure (NPT-Non punch-through IGBT)
- Low tail current with low temperature dependence
- Low threshold voltage

### Typical Applications*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



**GARL**

| Absolute Maximum Ratings | | | $T_s$ = 25 °C, unless otherwise specified | |
|---|---|---|---|---|
| **Symbol** | **Conditions** | | **Values** | **Units** |
| **IGBT** | | | | |
| $V_{CES}$ | $T_j$ = 25 °C | | 600 | V |
| $I_C$ | $T_j$ = 125 °C | $T_s$ = 25 °C | 54 | A |
| | | $T_s$ = 80 °C | 40 | A |
| $I_{CRM}$ | $I_{CRM}$= 2 x $I_{Cnom}$ | | 120 | A |
| $V_{GES}$ | | | ± 20 | V |
| $t_{psc}$ | $V_{CC}$ = 300 V; $V_{GE} \leq$ 20 V; $V_{CES}$ < 600 V | $T_j$ = 125 °C | 10 | µs |
| **Inverse Diode** | | | | |
| $I_F$ | $T_j$ = 150 °C | $T_s$ = 25 °C | 25 | A |
| | | $T_s$ = 80 °C | 17 | A |
| $I_{FRM}$ | $I_{FRM}$= 2 x $I_{Fnom}$ | | | A |
| $I_{FSM}$ | $t_p$ = 10 ms; half sine wave | $T_j$ = 150 °C | 100 | A |
| **Freewheeling Diode** | | | | |
| $I_F$ | $T_j$ = 150 °C | $T_s$ = 25 °C | 64 | A |
| | | $T_s$ = 80 °C | 48 | A |
| $I_{FRM}$ | | | | A |
| $I_{FSM}$ | $t_p$ = 10 ms; half sine wave | $T_j$ = 150 °C | 400 | A |
| **Module** | | | | |
| $I_{t(RMS)}$ | | | | A |
| $T_{vj}$ | | | -40 ... +150 | °C |
| $T_{stg}$ | | | -40 ... +125 | °C |
| $V_{isol}$ | AC, 1 min. | | 2500 | V |

| Characteristics | | | $T_s$ = 25 °C, unless otherwise specified | | | |
|---|---|---|---|---|---|---|
| **Symbol** | **Conditions** | | **min.** | **typ.** | **max.** | **Units** |
| **IGBT** | | | | | | |
| $V_{GE(th)}$ | $V_{GE}$ = $V_{CE}$, $I_C$ = 0,7 mA | | 3 | 4 | 5 | V |
| $I_{CES}$ | $V_{GE}$ = 600 V, $V_{CE}$ = $V_{CES}$ | $T_j$ = 25 °C | | | 0,0022 | mA |
| $I_{GES}$ | $V_{CE}$ = 0 V, $V_{GE}$ = 20 V | $T_j$ = 25 °C | | | 120 | nA |
| $V_{CE0}$ | | $T_j$ = 25 °C | | 1,2 | 1,3 | V |
| | | $T_j$ = 125 °C | | 1,1 | 1,2 | V |
| $r_{CE}$ | $V_{GE}$ = 15 V | $T_j$ = 25°C | | | 12 | mΩ |
| | | $T_j$ = 125°C | | | 22 | mΩ |
| $V_{CE(sat)}$ | $I_{Cnom}$ = 60 A, $V_{GE}$ = 15 V | $T_j$ = 25°C$_{chiplev.}$ | | 1,7 | 2 | V |
| | | $T_j$ = 125°C$_{chiplev.}$ | | 2,2 | 2,2 | V |
| $C_{ies}$ | $V_{CE}$ = 25, $V_{GE}$ = 0 V | f = 1 MHz | | 3,2 | | nF |
| $C_{oes}$ | | | | 0,3 | | nF |
| $C_{res}$ | | | | 0,18 | | nF |
| $Q_G$ | $V_{GE}$=0 ... 20 V | | | 375 | | nC |
| $t_{d(on)}$ | $R_{Gon}$ = 15 Ω | $V_{CC}$ = 300V | | 47 | | ns |
| $t_r$ | | $I_C$= 40A | | 60 | 80 | ns |
| $E_{on}$ | | $T_j$ = 125 °C | | 1,07 | 1,4 | mJ |
| $t_{d(off)}$ | $R_{Goff}$ = 16 Ω | $V_{GE}$= ±15V | | 220 | 280 | ns |
| $t_f$ | | | | 20 | 26 | ns |
| $E_{off}$ | | | | 0,76 | 1 | mJ |
| $R_{th(j-s)}$ | per IGBT | | | | 0,85 | K/W |

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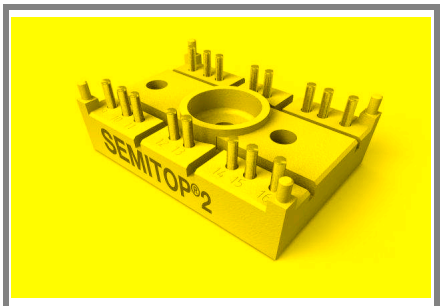


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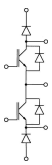

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**Characteristics**

| Symbol | Conditions | | min. | typ. | max. | Units |
|---|---|---|---|---|---|---|
| **Inverse Diode** | | | | | | |
| $V_F = V_{EC}$ | $I_{Fnom}$ = 15 A; $V_{GE}$ = 0 V | $T_j$ = 25 °$C_{chiplev.}$ | | 1,4 | 1,7 | V |
| | | $T_j$ = 125 °$C_{chiplev.}$ | | 1,4 | 1,7 | V |
| $V_{F0}$ | | $T_j$ = 125 °C | | 0,9 | 1 | V |
| $r_F$ | | $T_j$ = 125 °C | | 33 | 47 | mΩ |
| $I_{RRM}$ | $I_F$ = 30 A | $T_j$ = 125 °C | | | | A |
| $Q_{rr}$ | di/dt = 500 A/µs | | | | | µC |
| $E_{rr}$ | $V_{CC}$=300V | | | | | mJ |
| $R_{th(j-s)D}$ | per diode | | | | 2,3 | K/W |
| **Freewheeling diode** | | | | | | |
| $V_F = V_{EC}$ | $I_{Fnom}$ = 60 A; $V_{GE}$ = 0 V | $T_j$ = 25 °$C_{chiplev.}$ | | 1,45 | 1,7 | V |
| | | $T_j$ = 150 °$C_{chiplev.}$ | | 1,4 | 1,75 | V |
| $V_{F0}$ | | $T_j$ = 125 °C | | 0,85 | 0,9 | V |
| $r_F$ | | $T_j$ = 125 °C | | 11 | 16 | V |
| $I_{RRM}$ | $I_F$ = 50 A | $T_j$ = 125 °C | | 40 | | A |
| $Q_{rr}$ | di/dt = -1000 A/µs | | | 3,6 | | µC |
| $E_{rr}$ | $V_R$=300V | | | 0,55 | | mJ |
| $R_{th(j-s)D}$ | per diode | | | | 1,1 | K/W |
| $M_s$ | to heat sink | | 1,8 | | 2 | Nm |
| w | | | | 19 | | g |

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

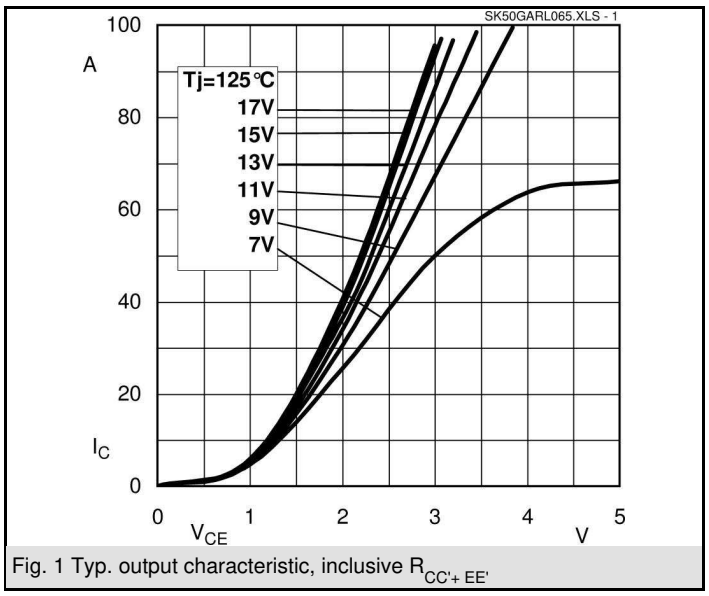



Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

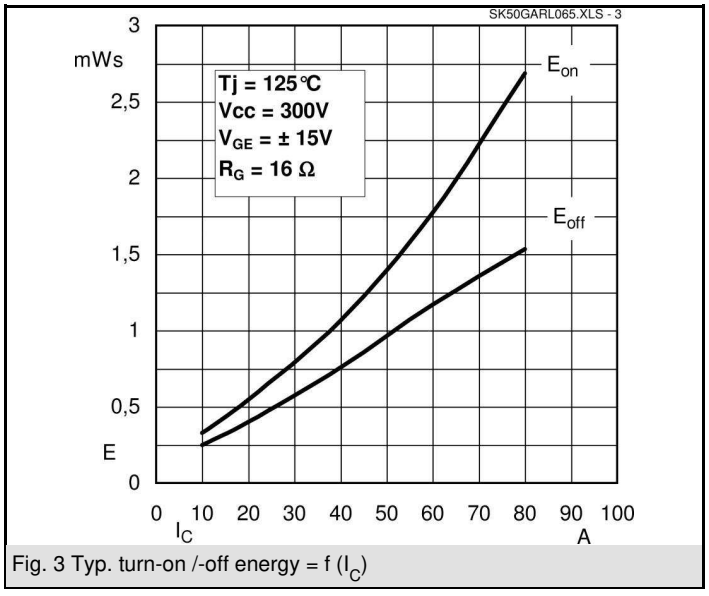



Fig. 3 Typ. turn-on /-off energy = f ($I_C$)

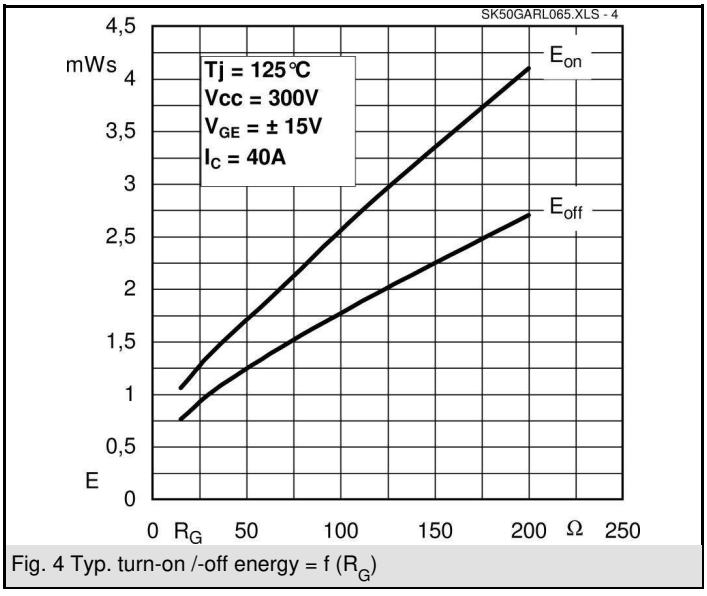



Fig. 4 Typ. turn-on /-off energy = f ($R_G$)

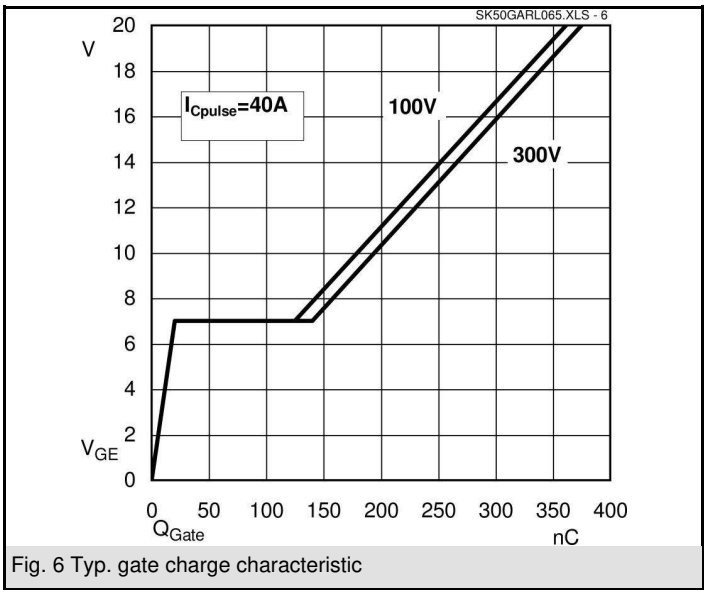



Fig. 6 Typ. gate charge characteristic

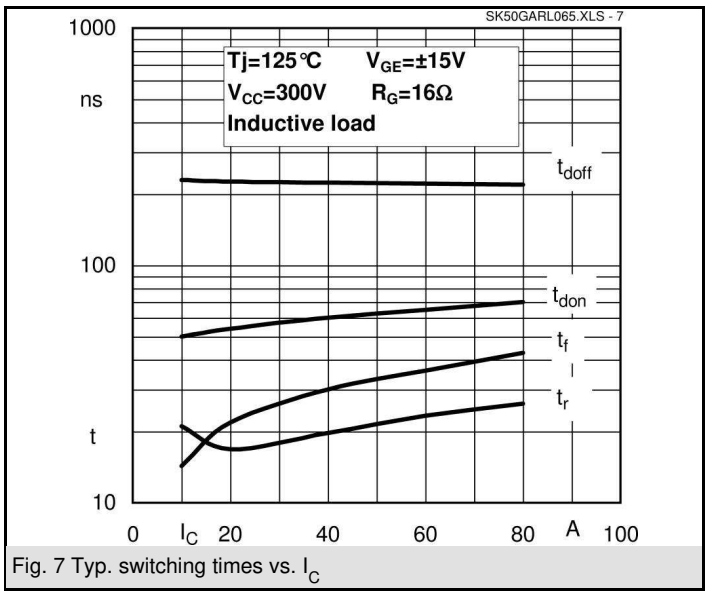


Fig. 7 Typ. switching times vs. $I_C$

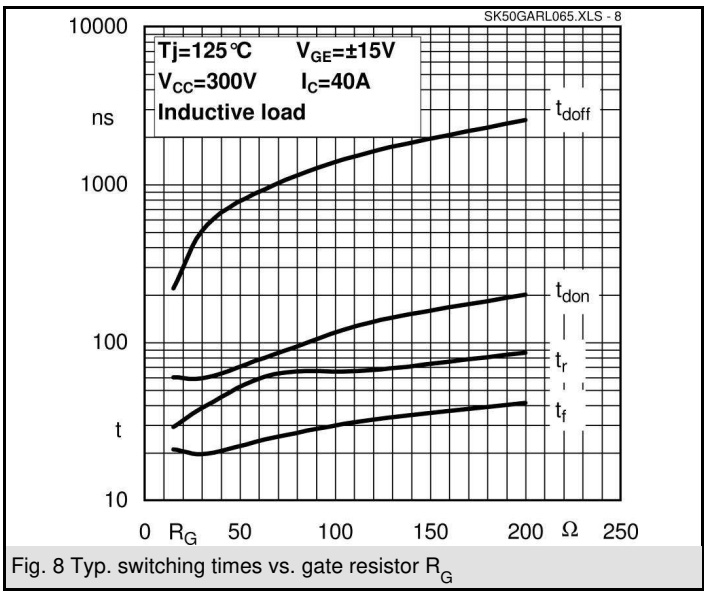


Fig. 8 Typ. switching times vs. gate resistor $R_G$

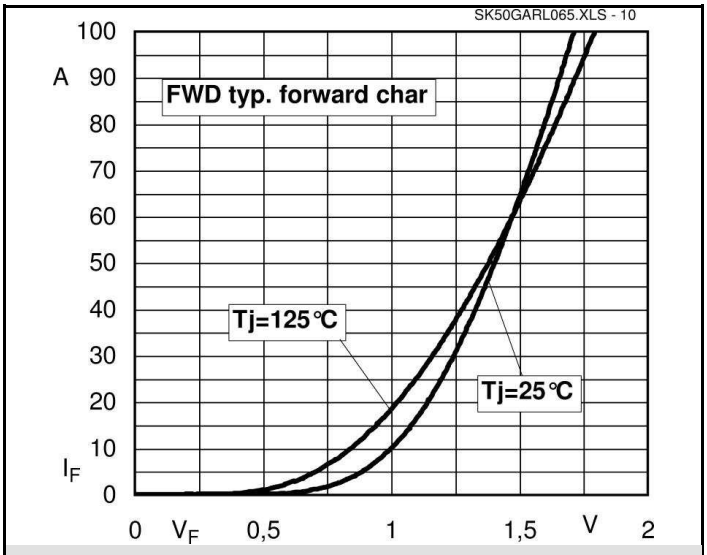
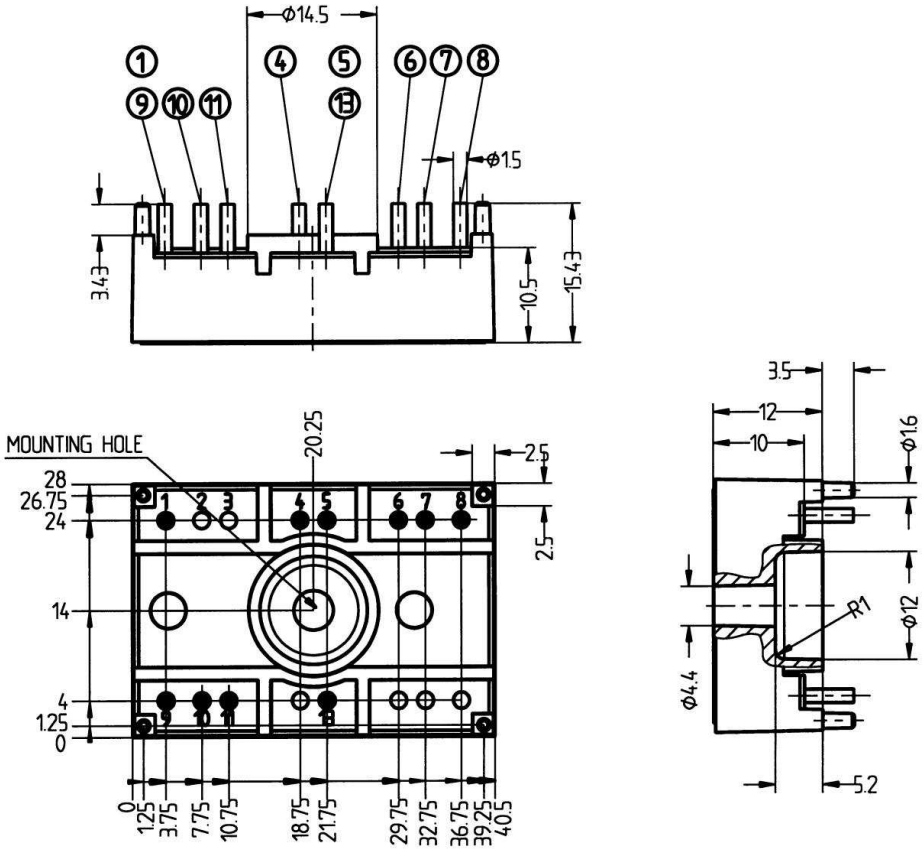


Fig. 10 CAL diode forward characteristic

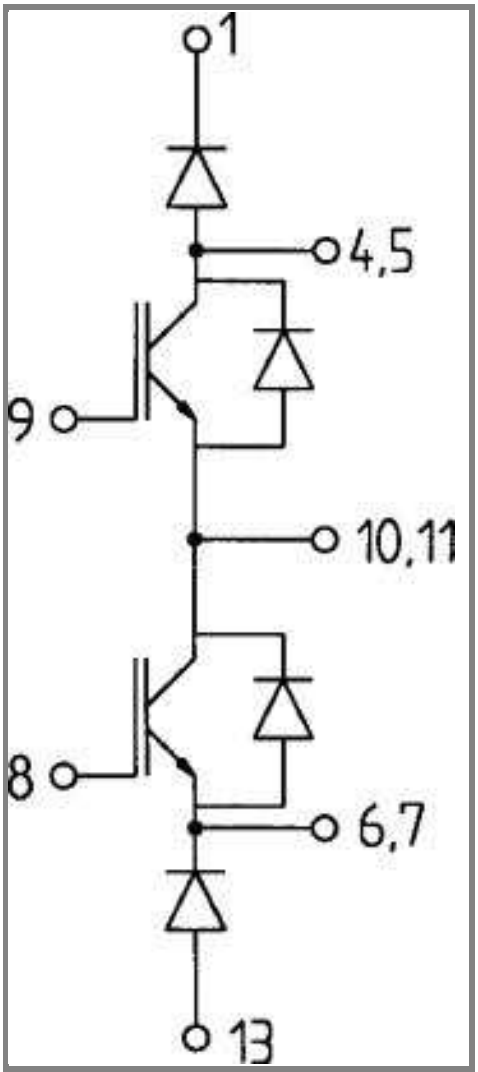
 

UL recognized file no. E 63 532




Case T31 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)




Case T31 GARL